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Title: THYRISTOR-BASED SRAM AND METHOD FOR THE FABRICATION THEREOF

Inventors: Elgin Quek, et al. Docket No.: 1016-028

Contact: Mikio Ishimaru

(408) 738-0592

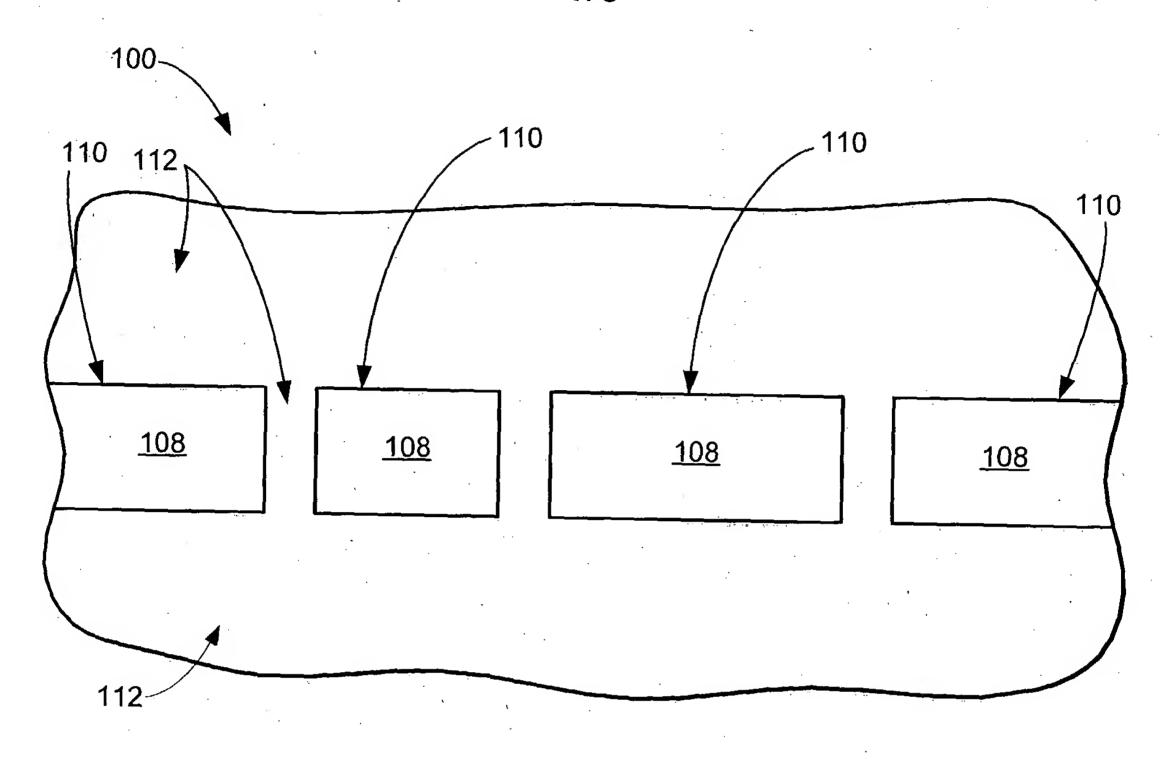


FIG. 1B

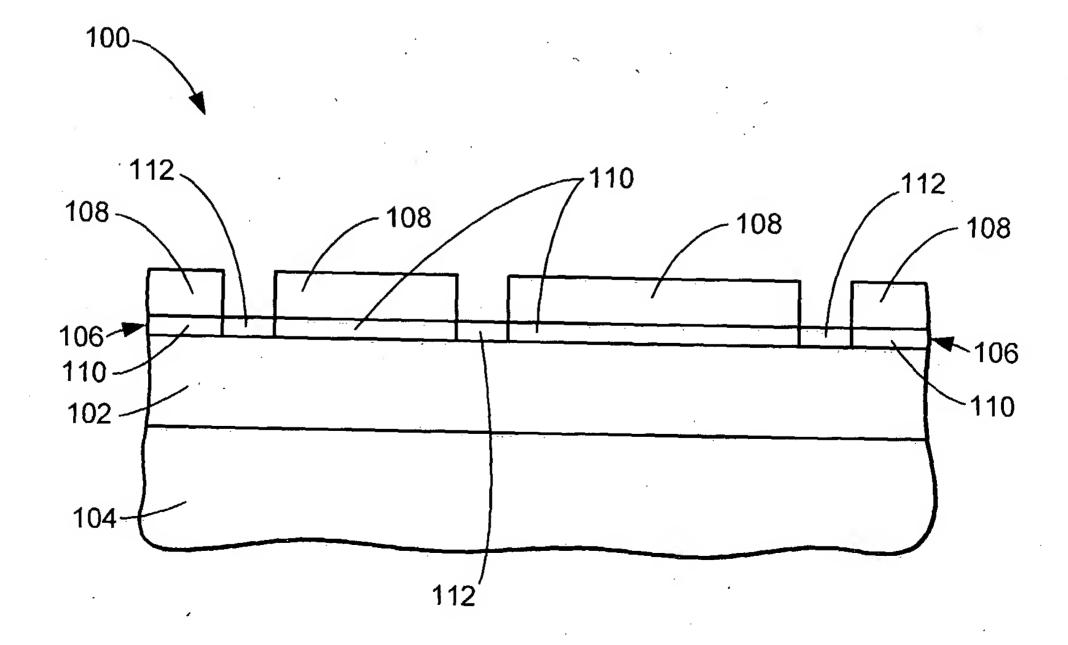


FIG. 1A

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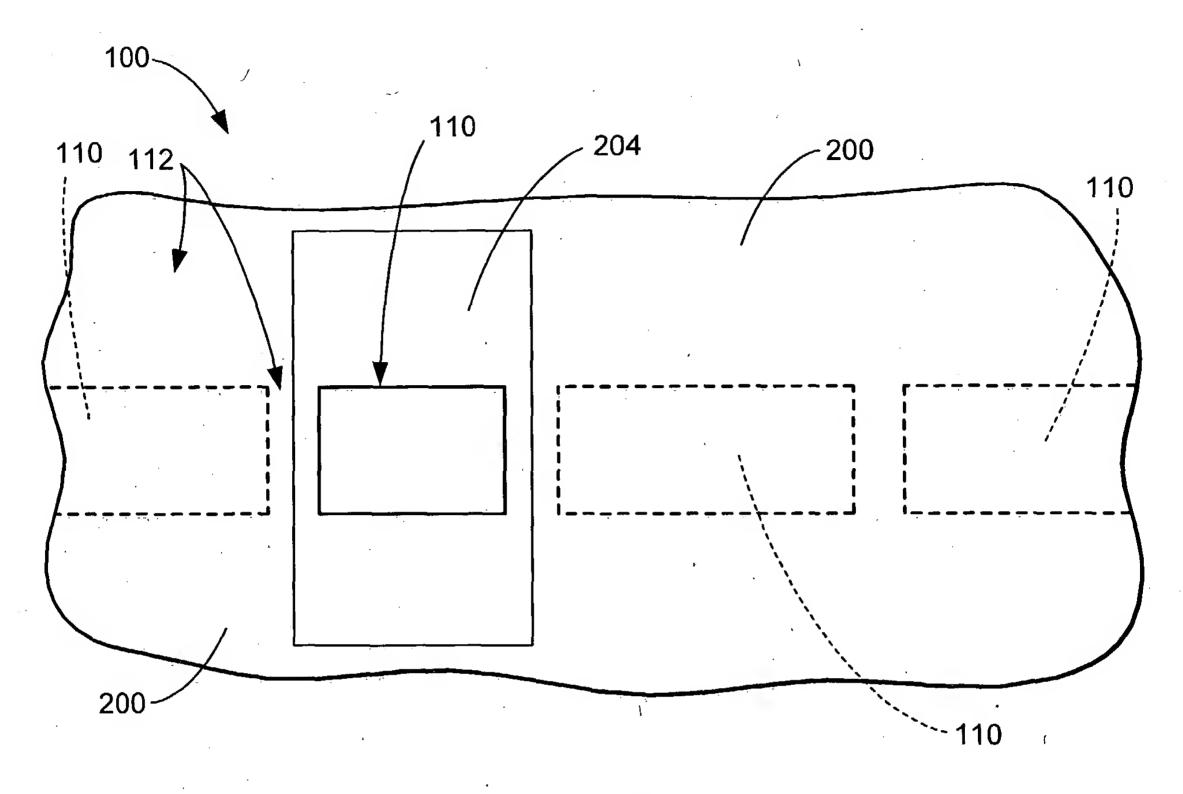


FIG. 2B

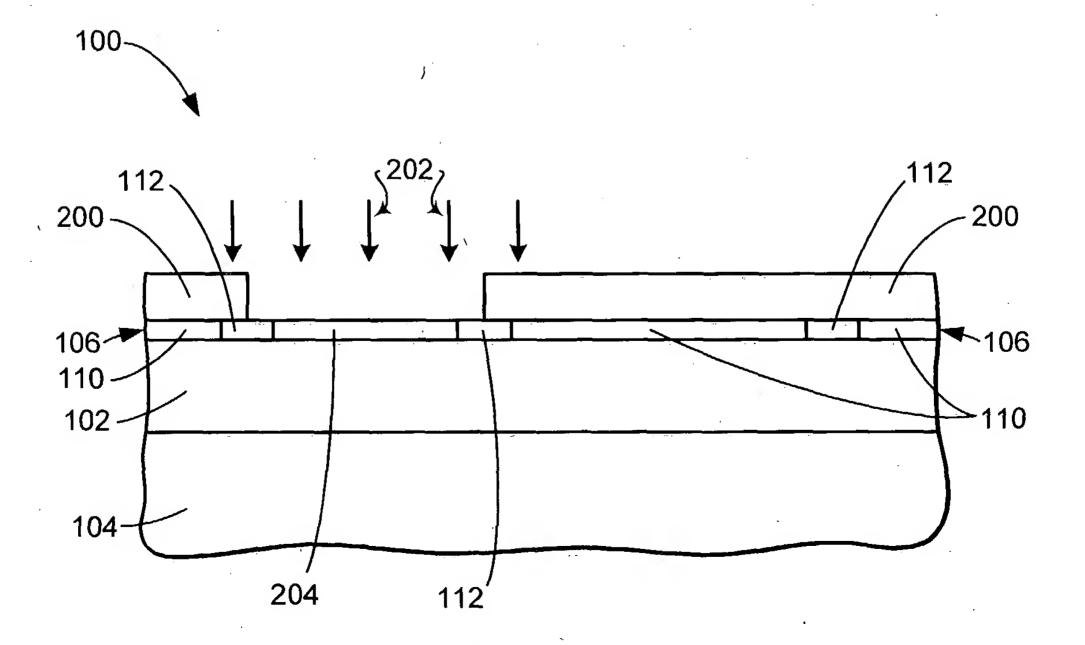


FIG. 2A

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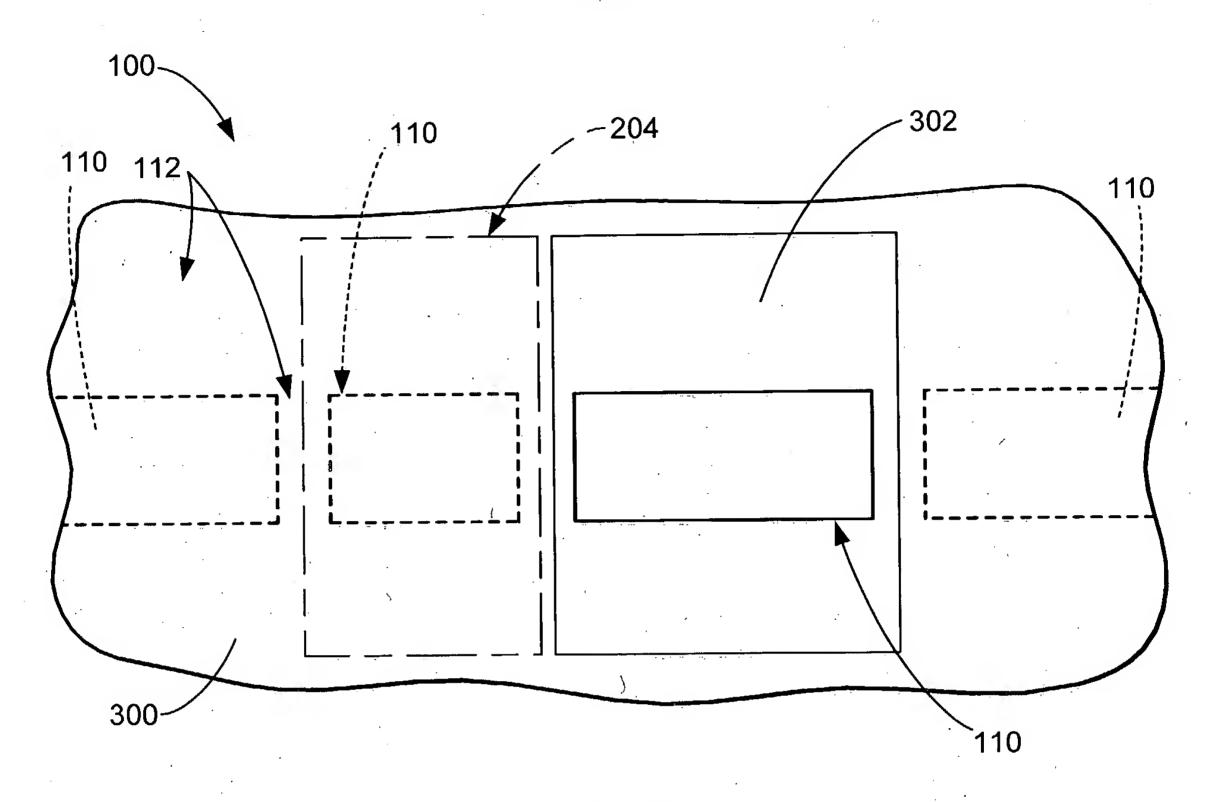


FIG. 3B

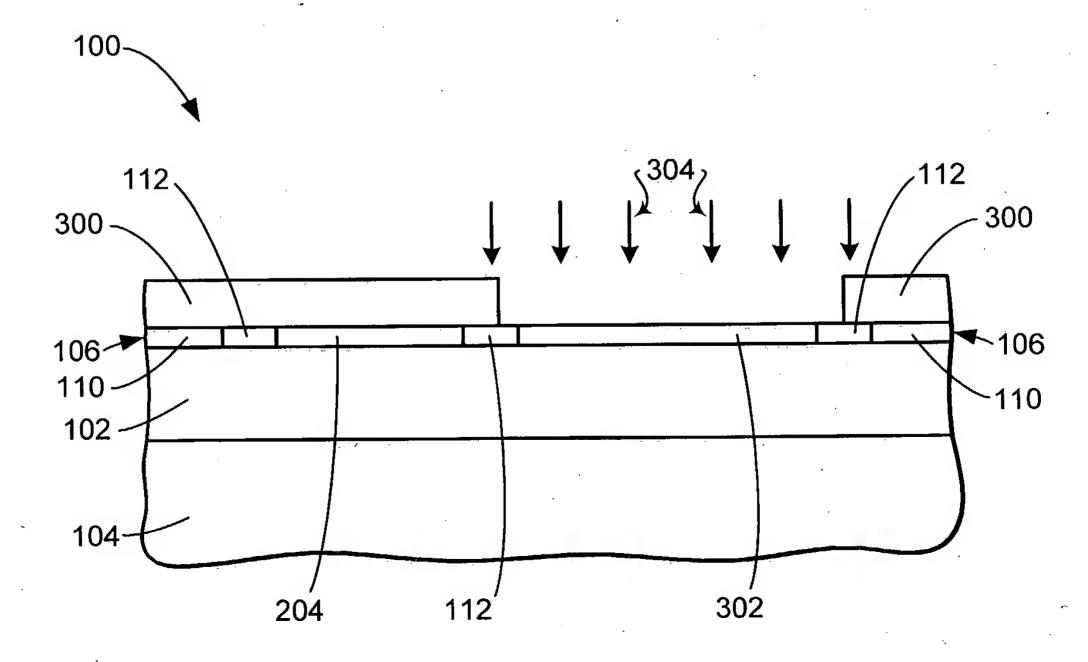


FIG. 3A

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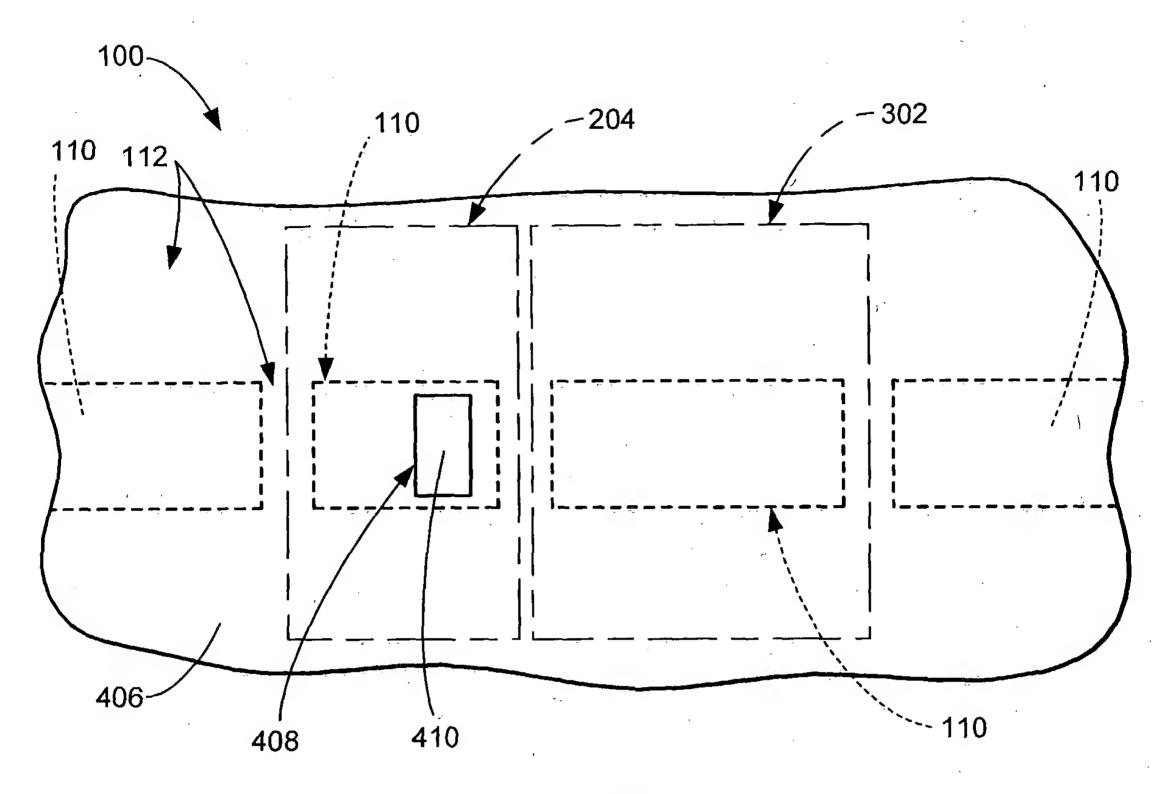


FIG. 4B

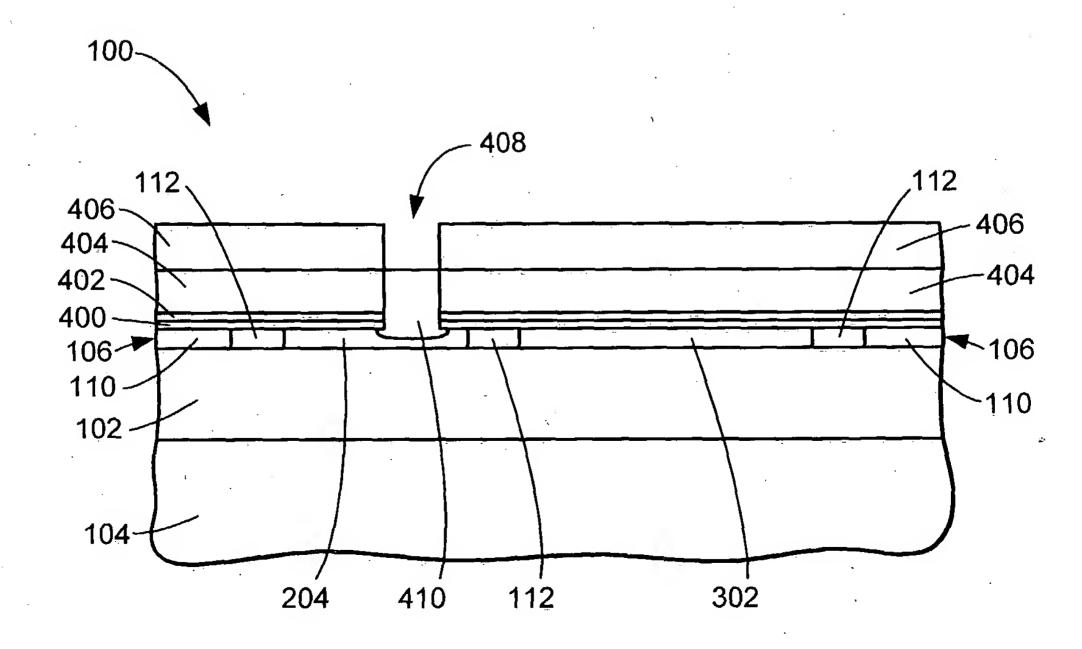


FIG. 4A

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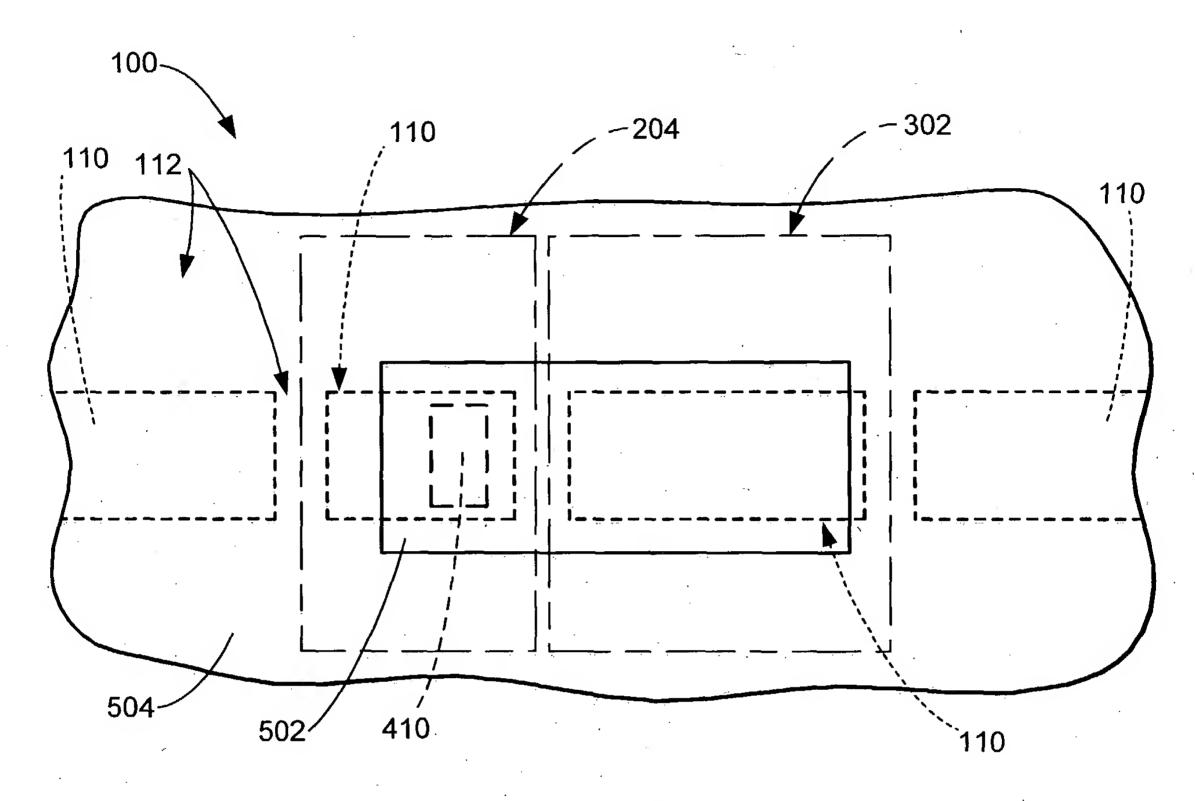
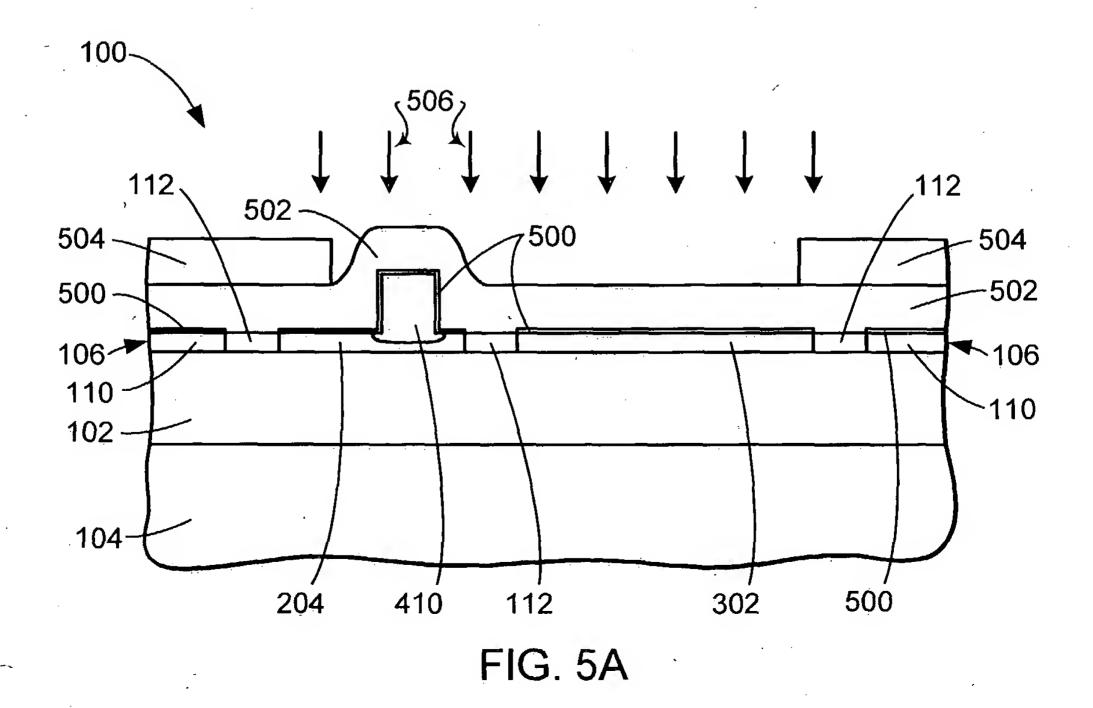


FIG. 5B



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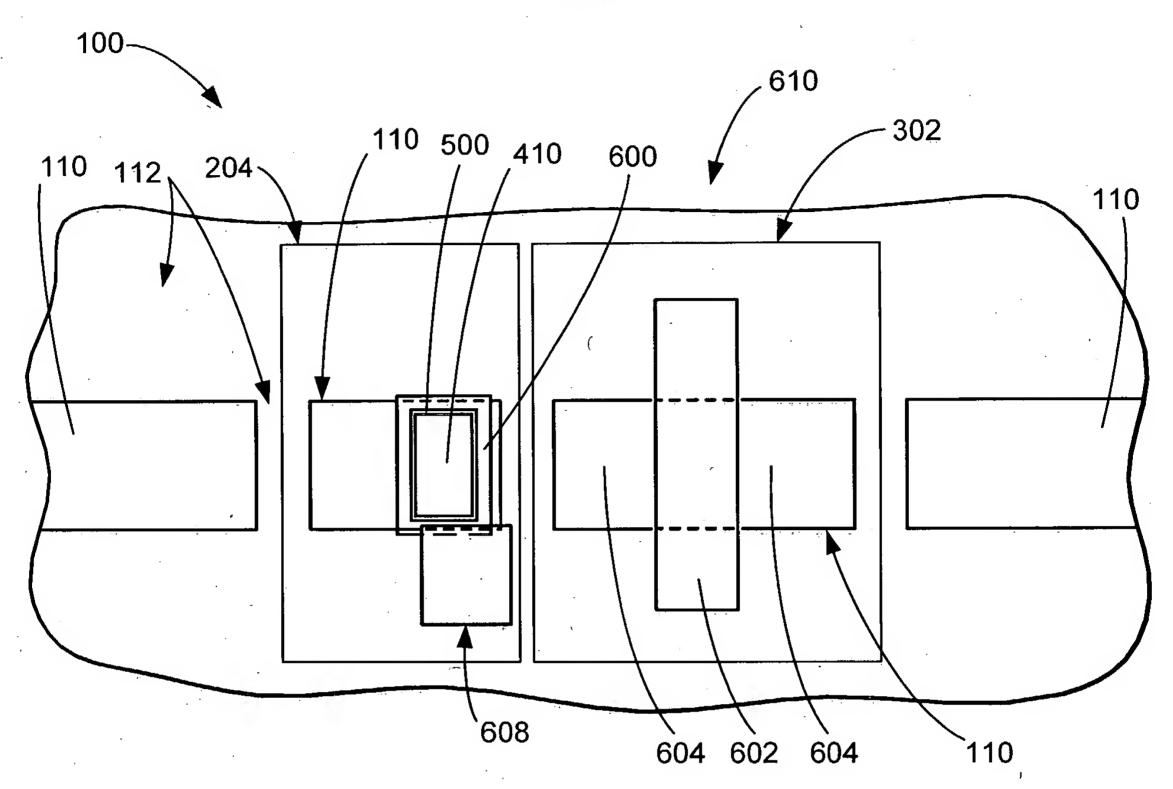
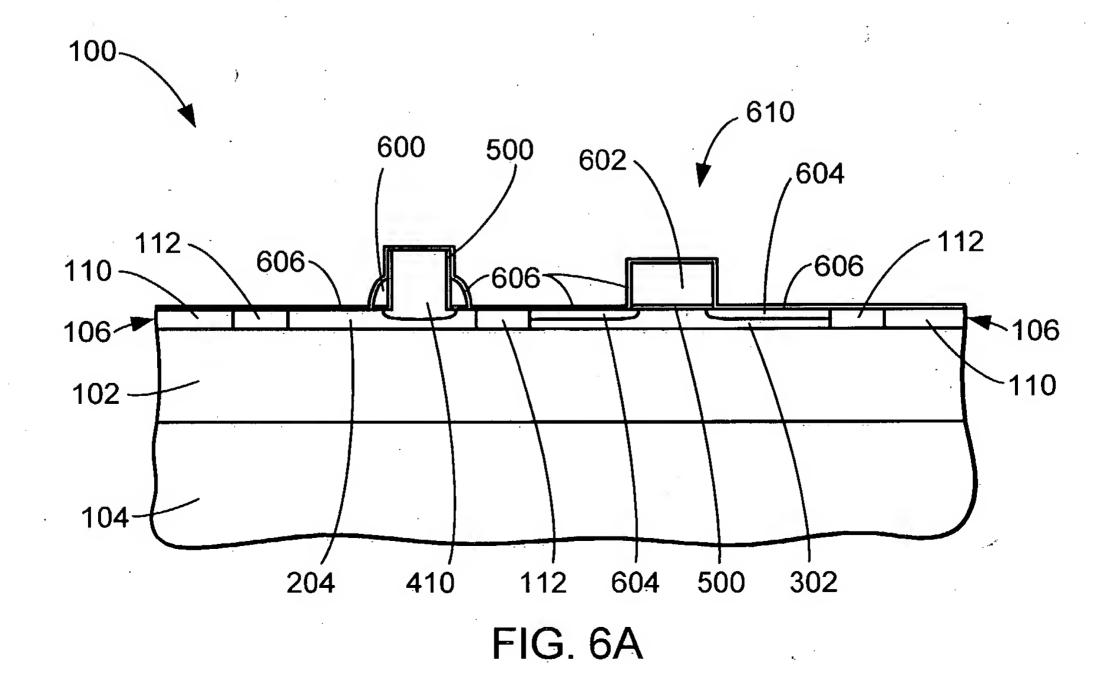


FIG. 6B



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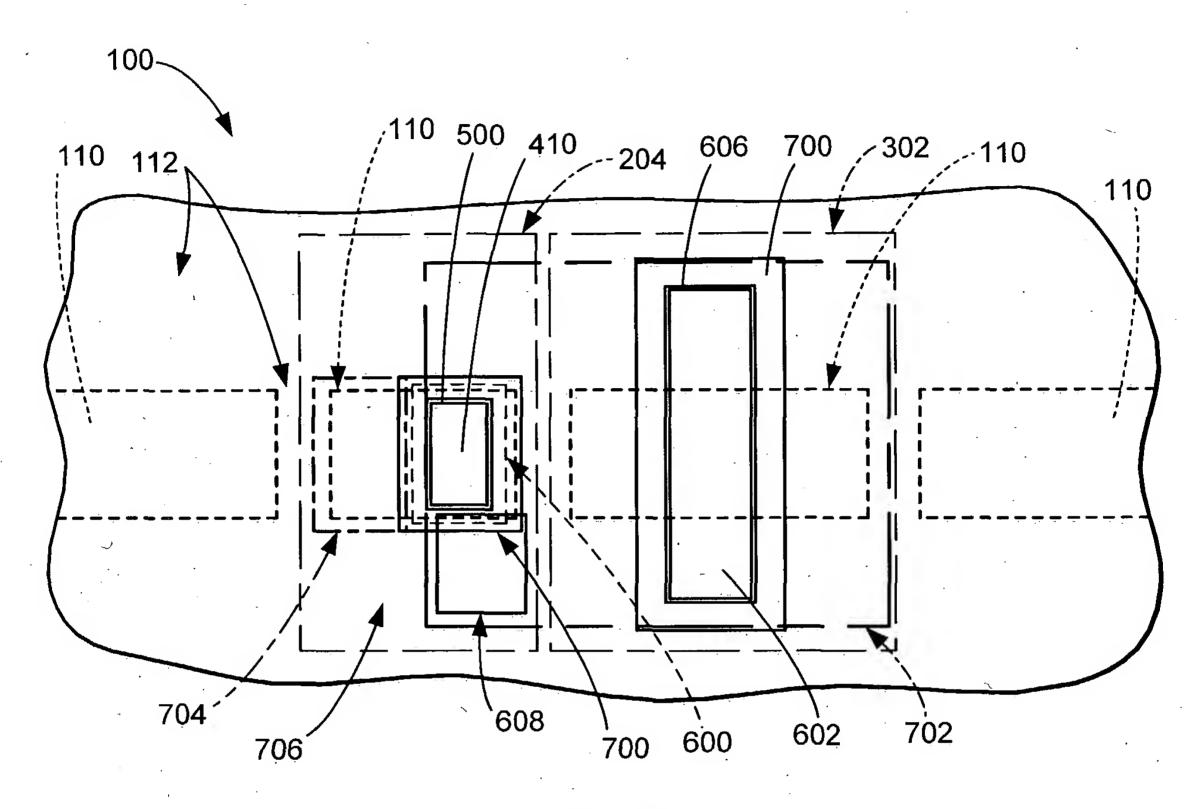


FIG. 7B

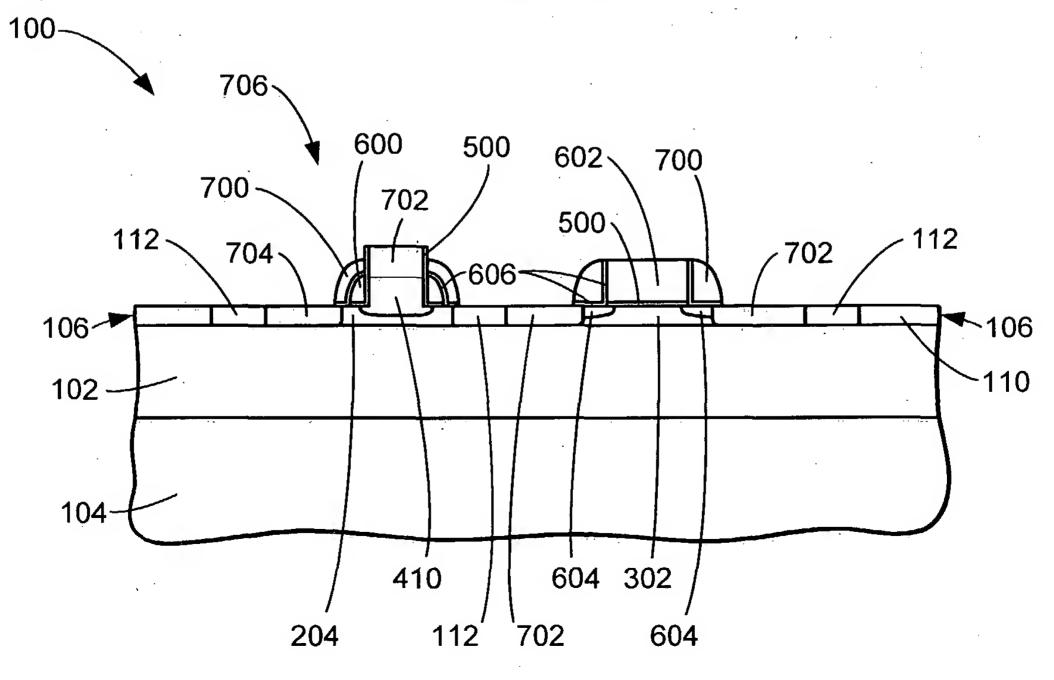


FIG. 7A

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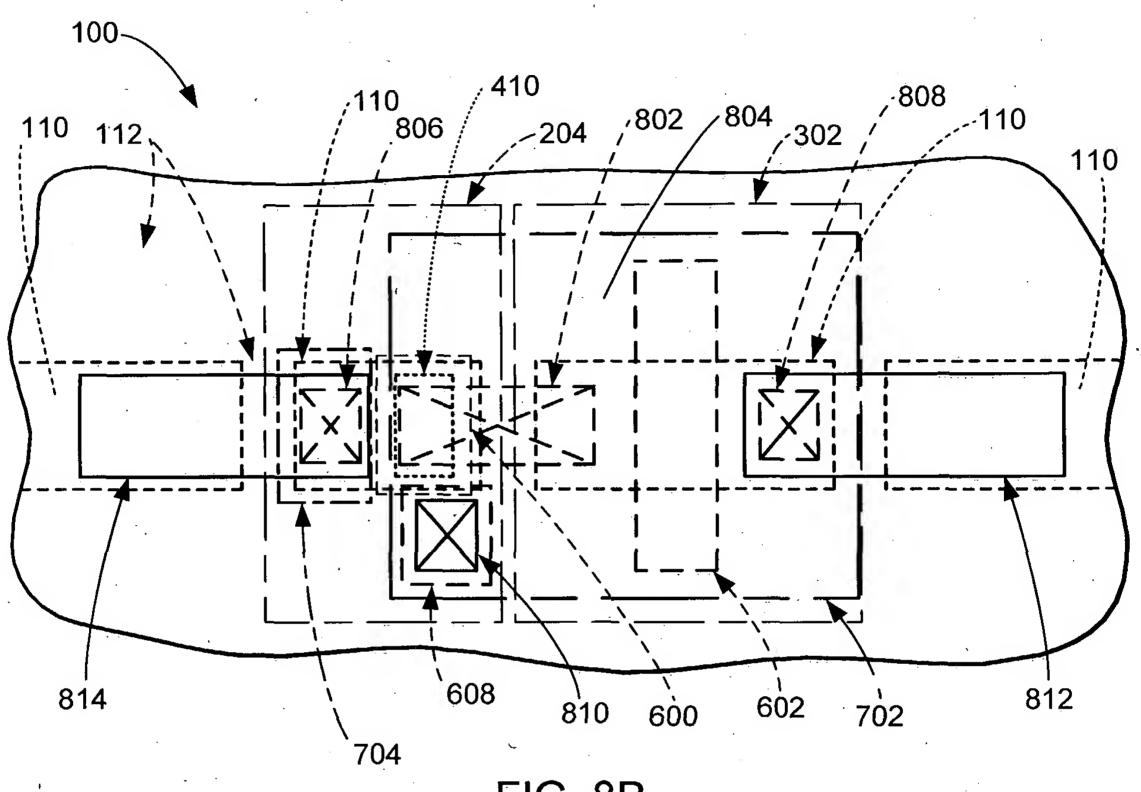


FIG. 8B

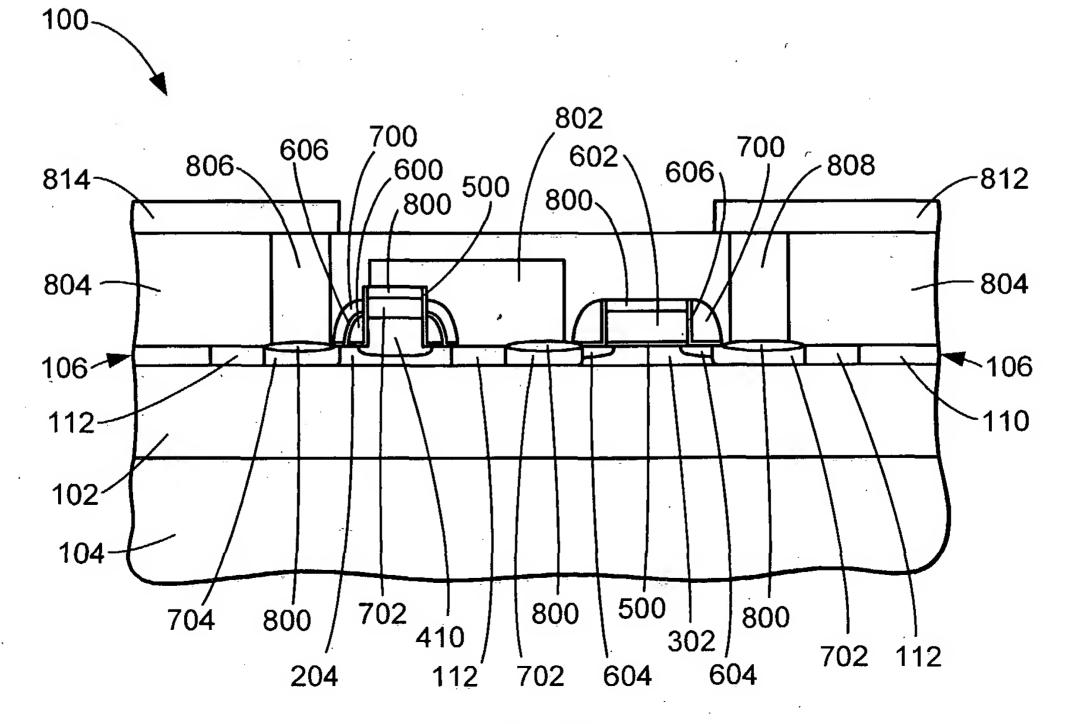


FIG. 8A

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900

PROVIDING A SEMICONDUCTOR SUBSTRATE $\underline{902}$

FORMING A THYRISTOR HAVING AT LEAST FOUR LAYERS WITH THREE P-N JUNCTIONS THEREBETWEEN, AT LEAST TWO OF THE LAYERS BEING FORMED HORIZONTALLY ON THE SEMICONDUCTOR SUBSTRATE AND AT LEAST TWO OF THE LAYERS BEING FORMED VERTICALLY ON THE SEMICONDUCTOR SUBSTRATE

<u>904</u>

FORMING A GATE ADJACENT AT LEAST ONE OF THE VERTICALLY FORMED LAYERS

906

FORMING AN ACCESS TRANSISTOR ON THE SEMICONDUCTOR SUBSTRATE

908

FORMING AN INTERCONNECT BETWEEN THE THYRISTOR AND THE ACCESS TRANSISTOR

910